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2811  
#13/C

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. Of: ITO  
Serial No.: 09/735,005  
Filed: December 12, 2000  
For: SEMICONDUCTOR DEVICE HAVING DUMMY GATES...  
Group: 2811  
Examiner: GEBREMARIAM, SAMUEL A. DOCKET: NEC 444

5/21/03  
Smith

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

AMENDMENT D

Dear Sir:

This Amendment is being filed in response to the Official Action mailed  
February 13, 2003.

Please amend the Application as follows:

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 5, line 23, with the following rewritten  
paragraph:

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--Finally, referring to Fig. 3C, the photoresist layer 203 is removed. Thus, the gate  
conductive layer 202 has gate patterns P1 and P2 corresponding to the gate patterns GP1 and  
GP2, respectively, and also, has dummy gates DG corresponding to the dummy gate patterns  
DP.--

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